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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

| Product Status | Active |
|----------------------------|---|
| Core Processor | ARM® Cortex®-M0+ |
| Core Size | 32-Bit Single-Core |
| Speed | 32MHz |
| Connectivity | I ² C, IrDA, LINbus, SPI, UART/USART |
| Peripherals | Brown-out Detect/Reset, DMA, POR, PWM, WDT |
| Number of I/O | 15 |
| Program Memory Size | 16KB (16K x 8) |
| Program Memory Type | FLASH |
| EEPROM Size | 1K x 8 |
| RAM Size | 8K x 8 |
| Voltage - Supply (Vcc/Vdd) | 1.8V ~ 3.6V |
| Data Converters | A/D 10x12b |
| Oscillator Type | Internal |
| Operating Temperature | -40°C ~ 85°C (TA) |
| Mounting Type | Surface Mount |
| Package / Case | 20-TSSOP (0.173", 4.40mm Width) |
| Supplier Device Package | 20-TSSOP |
| Purchase URL | https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l031f4p6 |

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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2 Description

The access line ultra-low-power STM32L031x4/6 family incorporates the high-performance ARM[®] Cortex[®]-M0+ 32-bit RISC core operating at a 32 MHz frequency, high-speed embedded memories (up to 32 Kbytes of Flash program memory, 1 Kbytes of data EEPROM and 8 Kbytes of RAM) plus an extensive range of enhanced I/Os and peripherals.

The STM32L031x4/6 devices provide high power efficiency for a wide range of performance. It is achieved with a large choice of internal and external clock sources, an internal voltage adaptation and several low-power modes.

The STM32L031x4/6 devices offer several analog features, one 12-bit ADC with hardware oversampling, two ultra-low-power comparators, several timers, one low-power timer (LPTIM), three general-purpose 16-bit timers, one RTC and one SysTick which can be used as timebases. They also feature two watchdogs, one watchdog with independent clock and window capability and one window watchdog based on bus clock.

Moreover, the STM32L031x4/6 devices embed standard and advanced communication interfaces: one I2C, one SPI, one USART, and a low-power UART (LPUART).

The STM32L031x4/6 also include a real-time clock and a set of backup registers that remain powered in Standby mode.

The ultra-low-power STM32L031x4/6 devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +125 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.







2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of core and features, from 8-bit proprietary core up to ARM[®] Cortex[®]-M4, including ARM[®] Cortex[®]-M3 and ARM[®] Cortex[®]-M0+. The STM32Lx series are the best choice to answer your needs in terms of ultra-low-power features. The STM32 Ultra-low-power series are the best solution for applications such as gas/water meter, keyboard/mouse or fitness and healthcare application. Several built-in features like LCD drivers, dual-bank memory, low-power run mode, operational amplifiers, 128-bit AES, DAC, crystal-less USB and many other definitely help you building a highly cost optimized application by reducing BOM cost. STMicroelectronics, as a reliable and long-term manufacturer, ensures as much as possible pin-to-pin compatibility between all STM8Lx and STM32Lx on one hand, and between all STM32Lx and STM32Fx on the other hand. Thanks to this unprecedented scalability, your legacy application can be upgraded to respond to the latest market feature and efficiency requirements.



3.5 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

Clock prescaler

To get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler.

• Safe clock switching

Clock sources can be changed safely on the fly in Run mode through a configuration register.

Clock management

To reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.

• System clock source

Three different clock sources can be used to drive the master clock SYSCLK:

- 1-25 MHz high-speed external (HSE), that can supply a PLL
- 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
- Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz).
 When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.

• Auxiliary clock source

Two ultra-low-power clock sources that can be used to drive the real-time clock:

- 32.768 kHz low-speed external crystal (LSE)
- 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.

RTC clock sources

The LSI, LSE or HSE sources can be chosen to clock the RTC, whatever the system clock.

• Startup clock

After reset, the microcontroller restarts by default with an internal 2 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.

• Clock security system (CSS)

This feature can be enabled by software. If an HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled. Another clock security system can be enabled, in case of failure of the LSE it provides an interrupt or wakeup event which is generated if enabled.

Clock-out capability (MCO: microcontroller clock output)

It outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.



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3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.14.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.15 Communication interfaces

3.15.1 I²C bus

One I²C interface (I2C1) can operate in multimaster or slave modes. The I²C interface can support Standard mode (Sm, up to 100 kbit/s), Fast mode (Fm, up to 400 kbit/s) and Fast Mode Plus (Fm+, up to 1 Mbit/s) with 20 mA output drive on some I/Os.

The I²C interface supports 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (2 addresses, 1 with configurable mask). They also include programmable analog and digital noise filters.

| | Analog filter | Digital filter |
|-------------------------------------|---|--|
| Pulse width of suppressed spikes | ≥ 50 ns | Programmable length from 1 to 15 I2C peripheral clocks |
| Benefits | Available in Stop mode | Extra filtering capability vs. standard requirements. Stable length |
| Drawbacks | Variations depending on temperature, voltage, process | Wakeup from Stop on address match is not available when digital filter is enabled. |

| Table 1 | 0 Com | narison | of I2C | analog | and | digital | filters |
|---------|----------|---------|--------|--------|-----|---------|---------|
| | 0. 00111 | parison | | analog | ana | ungitai | Inter 3 |

In addition, I2C1 provides hardware support for SMBus 2.0 and PMBus 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts verifications and ALERT protocol management. I2C1 also has a clock domain independent from the CPU clock, allowing the I2C1 to wake up the MCU from Stop mode on address match.

The I2C interface can be served by the DMA controller.

Refer to *Table 11* for the supported modes and features of I2C interface.



| | | Pin | Num | ber | | | | | | | | |
|---------|------------------------|----------|--------------------------------|--------|-------------------------|--------|---------------------------------------|-------------|---------------|------|---|----------------------|
| TSSOP20 | MLCSP25 ⁽¹⁾ | UFQFPN28 | UFQFPN28 (STM32L031GxUxS only) | LQFP32 | UFQFPN32 ⁽²⁾ | LQFP48 | Pin name (function after reset) | Pin type | I/O structure | Note | Alternate functions | Additional functions |
| - | - | - | - | - | - | 27 | PB14 | I/O | FT | - | SPI1_MISO, RTC_OUT, TIM21_CH2, LPUART1_RTS | - |
| - | - | - | - | - | - | 28 | PB15 | I/O | FT | - | SPI1_MOSI, RTC_REFIN | - |
| _ | C1 | 18 | 18 | 18 | 18 | 29 | PA8 | I/O | FT | - | MCO, LPTIM1_IN1, EVENTOUT, USART2_CK, TIM2_CH1 | - |
| 17 | B1 | 19 | 19 | 19 | 19 | 30 | PA9 | I/O | FTf | - | MCO, I2C1_SCL, USART2_TX, TIM22_CH1 | - |
| 18 | C2 | 20 | 20 | 20 | 20 | 31 | PA10 | I/O | FTf | - | I2C1_SDA, USART2_RX, TIM22_CH2 | - |
| - | - | - | - | 21 | 21 | 32 | PA11 | I/O | FT | - | SPI1_MISO, EVENTOUT, USART2_CTS, TIM21_CH2, COMP1_OUT | - |
| - | - | - | - | 22 | 22 | 33 | PA12 | I/O | FT | - | SPI1_MOSI, EVENTOUT, USART2_RTS, COMP2_OUT | - |
| 19 | A1 | 21 | 21 | 23 | 23 | 34 | PA13 | I/O | FT | - | SWDIO, LPTIM1_ETR, LPUART1_RX | - |

Table 15. Pin definitions (continued)



| Symbol | Ratings | Max. | Unit |
|----------------------------------|--|----------------------|------|
| $\Sigma I_{VDD}^{(2)}$ | Total current into sum of all V_{DD} power lines (source) ⁽¹⁾ | 105 | |
| ΣI _{VSS} ⁽²⁾ | Total current out of sum of all V_{SS} ground lines (sink) ⁽¹⁾ | 105 | |
| I _{VDD(PIN)} | Maximum current into each V _{DD} power pin (source) ⁽¹⁾ | 100 | |
| I _{VSS(PIN)} | Maximum current out of each V_{SS} ground pin (sink) ⁽¹⁾ | 100 | |
| | Output current sunk by any I/O and control pin except FTf pins | 16 | |
| l _{iO} | Output current sunk by FTf pins | 22 | |
| | Output current sourced by any I/O and control pin | -16 | |
| 51 (3) | Total output current sunk by sum of all IOs and control pins ⁽⁴⁾ | 45 m/ | |
| ∠iio(pin)` ′ | Total output current sourced by sum of all IOs and control pins ⁽⁴⁾ | -45 | |
| ΣL ⁽⁵⁾ | Total output current sunk by sum of all IOs and control pins ⁽²⁾ | 90 | |
| ∠IO(PIN) | Total output current sourced by sum of all IOs and control pins ⁽²⁾ | -90 | |
| I | Injected current on FT, FFf, RST and B pins | -5/+0 ⁽⁶⁾ | |
| 'INJ(PIN) | Injected current on TC pin | ± 5 ⁽⁷⁾ | |
| ΣΙ _{INJ(PIN)} | Total injected current (sum of all I/O and control pins) ⁽⁸⁾ | ± 25 | |

| Table 18. | Current | characteristics |
|-----------|---------|-----------------|
|-----------|---------|-----------------|

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.

- 3. These values apply only to STM32L031GxUxS part number.
- 4. This current consumption must be correctly distributed over all I/Os and control pins. In particular, it must be located the closest possible to the couple of supply and ground, and distributed on both sides.
- 5. These values apply to all part numbers except for STM32L031GxUxS.
- 6. Positive current injection is not possible on these I/Os. A negative injection is induced by V_{IN} <V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 17* for maximum allowed input voltage values.
- A positive injection is induced by V_{IN} > V_{DD} while a negative injection is induced by V_{IN} < V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 17: Voltage characteristics* for the maximum allowed input voltage values.
- 8. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 19. Thermal characteristics

| Symbol | Ratings | Value | Unit |
|------------------|------------------------------|-------------|------|
| T _{STG} | Storage temperature range | –65 to +150 | °C |
| TJ | Maximum junction temperature | 150 | °C |



| Symbol | Parameter | Conditions | Тур | Max ⁽¹⁾ | Unit |
|------------------------|-----------------------------|---------------------------------------|------|--------------------|------|
| | | $T_A = -40^{\circ}C$ to $25^{\circ}C$ | 0.38 | 0.99 | |
| I _{DD} (Stop) | Supply current in Stop mode | T _A = 55°C | 0.54 | 1.9 | |
| | | T _A = 85°C | 1.35 | 4.2 | μA |
| | | T _A = 105°C | 3.1 | 9 | |
| | | T _A = 125°C | 7.55 | 19 | |

Table 31. Typical and maximum current consumptions in Stop mode

1. Guaranteed by characterization results at 125 $^\circ\text{C},$ unless otherwise specified.

Figure 18. I_{DD} vs V_{DD}, at T_A= 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive



Figure 19. I_{DD} vs V_{DD}, at T_A= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks off



On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on

Table 34. Peripheral current consumption in Run or Sleep mode⁽¹⁾

| | | Туріс | | | | |
|-------------|---------------------|---|---|---|----------------------------|---------------------------------|
| Peripheral | | Range 1, V _{CORE} =1.8 V VOS[1:0] = 01 | Range 2, V _{CORE} =1.5 V VOS[1:0] = 10 | Range 3, V _{CORE} =1.2 V VOS[1:0] = 11 | Low-power sleep and run | Unit |
| | WWDG | 3 | 2 | 2 | 2 | |
| | LPUART1 | 8 | 6.5 | 5.5 | 6 | |
| | I2C1 | 11 | 9.5 | 7.5 | 9 | |
| AFDI | LPTIM1 | 10 | 8.5 | 6.5 | 8 | μΑλινίι ιz (i _{HCLK}) |
| | TIM2 | 10.5 | 8.5 | 7 | 9 | |
| | USART2 | 14.5 | 12 | 9.5 | 11 | |
| | ADC1 ⁽²⁾ | 5.5 | 5 | 3.5 | 4 | |
| | SPI1 | 4 | 3 | 3 | 2.5 | |
| | TIM21 | 7.5 | 6 | 5 | 5.5 | |
| APDZ | TIM22 | 7 | 6 | 5 | 6 | μΑλινίπz (I _{HCLK}) |
| | DBGMCU | 1.5 | 1 | 1 | 0.5 | |
| | SYSCFG | 2.5 | 2 | 2 | 1.5 | |
| | GPIOA | 3.5 | 3 | 2.5 | 2.5 | |
| Cortex- | GPIOB | 3.5 | 2.5 | 2 | 2.5 | $(A \wedge A) = (f \wedge A)$ |
| I/O port | GPIOC | 8.5 | 6.5 | 5.5 | 7 | μΑλινίπz (I _{HCLK}) |
| | GPIOH | 1.5 | 1 | 1 | 0.5 | |
| | CRC | 1.5 | 1 | 1 | 1 | |
| | FLASH | 0 ⁽³⁾ | 0 ⁽³⁾ | 0 ⁽³⁾ | 0 ⁽³⁾ | |
| АПБ | DMA1 | 10 | 8 | 6.5 | 8.5 | µA/MHz (f _{HCLK}) |
| All enabled | | 101 | 83 | 66 | 85 | |
| PWR | | 2.5 | 2 | 2 | 1 | µA/MHz (f _{HCLK}) |

Data based on differential I_{DD} measurement between all peripherals off an one peripheral with clock enabled, in the following conditions: f_{HCLK} = 32 MHz (range 1), f_{HCLK} = 16 MHz (range 2), f_{HCLK} = 4 MHz (range 3), f_{HCLK} = 64kHz (Low-power run/sleep), f_{APB1} = f_{HCLK}, f_{APB2} = f_{HCLK}, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling. Not tested in production.

2. HSI oscillator is off for this measure.

3. Current consumption is negligible and close to 0 μ A.



Electrical characteristics

| Symbol | Parameter | Conditions | Тур | Мах | Unit | |
|----------------------|--|--|-----|-----|--------------------|--|
| t _{WUSLEEP} | Wakeup from Sleep mode | f _{HCLK} = 32 MHz | 7 | 8 | | |
| twusleep | Wakeup from Low-power sleep mode, | f _{HCLK} = 262 kHz Flash memory enabled | 7 | 8 | Number of clock | |
| LP | f _{HCLK} = 262 kHz | ameterConditionso mode $f_{HCLK} = 32 \text{ MHz}$ o mode $f_{HCLK} = 262 \text{ kHz}$ power sleep mode, $f_{HCLK} = 262 \text{ kHz}$ Flash memory enabled $f_{HCLK} = 262 \text{ kHz}$ Flash memory switched OFF $f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ mode, regulator in Run $f_{HCLK} = f_{HSI} = 16 \text{ MHz}$ $f_{HCLK} = f_{HSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ $Voltage range 1$ $f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ $Voltage range 2$ $f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ $Voltage range 3$ $f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ $Voltage range 3$ $f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$ $f_{HCLK} = f_{MSI} = 1.05 \text{ MHz}$ $f_{HCLK} = f_{MSI} = 524 \text{ kHz}$ $f_{HCLK} = f_{MSI} = 105 \text{ MHz}$ $f_{HCLK} = f_{MSI} = 1262 \text{ kHz}$ $f_{HCLK} = f_{MSI} = 131 \text{ kHz}$ $f_{HCLK} = f_{MSI} = 131 \text{ kHz}$ $f_{HCLK} = f_{HSI} = 16 \text{ MHz}$ $f_{HCLK} = f_{HSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{HSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{HSI} = 16 \text{ MHz}$ $f_{HCLK} = f_{HSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{HSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{HSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{HSI} = 4.2 \text{ MHz}$ $f_{HCLK} = f_{MSI} = 4$ | 9 | 10 | cycles | |
| | | f _{HCLK} = f _{MSI} = 4.2 MHz | 5.0 | 8 | | |
| | Wakeup from Stop mode, regulator in Run mode | f _{HCLK} = f _{HSI} = 16 MHz | 4.9 | 7 | | |
| | | f _{HCLK} = f _{HSI} /4 = 4 MHz | 8.0 | 11 | | |
| | | f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 1 | 5.0 | 8 | | |
| | | f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 2 | 5.0 | 8 | | |
| | | f _{HCLK} = f _{MSI} = 4.2 MHz Voltage range 3 | 5.0 | 8 | μs | |
| | Wakeup from Stop mode, regulator in low- power mode | f _{HCLK} = f _{MSI} = 2.1 MHz | 7.3 | 13 | | |
| t _{WUSTOP} | | f _{HCLK} = f _{MSI} = 1.05 MHz | 13 | 23 | | |
| | | f _{HCLK} = f _{MSI} = 524 kHz | 28 | 38 | | |
| | | f _{HCLK} = f _{MSI} = 262 kHz | 51 | 65 | | |
| | | f _{HCLK} = f _{MSI} = 131 kHz | 100 | 120 | | |
| | | f _{HCLK} = MSI = 65 kHz | 200 | 260 | | |
| | | f _{HCLK} = f _{HSI} = 16 MHz | 4.9 | 7 | | |
| | | f _{HCLK} = f _{HSI} /4 = 4 MHz | 8.0 | 11 | | |
| | | f _{HCLK} = f _{HSI} = 16 MHz | 4.9 | 7 | | |
| | power mode, code running from RAM | f _{HCLK} = f _{HSI} /4 = 4 MHz | 7.9 | 10 | | |
| | | f _{HCLK} = f _{MSI} = 4.2 MHz | 4.7 | 8 | | |
| t | Wakeup from Standby mode FWU bit = 1 | f _{HCLK} = MSI = 2.1 MHz | 65 | 130 | | |
| WUSTDBY | Wakeup from Standby mode FWU bit = 0 | f _{HCLK} = MSI = 2.1 MHz | 2.2 | 3 | ms | |

| Table 30. Low-Dower mode wakeup ummus | Table 36. Lov | /-power mode | wakeup | timinas |
|---------------------------------------|---------------|--------------|--------|---------|
|---------------------------------------|---------------|--------------|--------|---------|



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 25 MHz crystal/ceramic resonator oscillator (LQFP48 package only). All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|------------------------|-----|-----|-----|----------|
| f _{OSC_IN} | Oscillator frequency | - | 1 | | 25 | MHz |
| R _F | Feedback resistor | - | - | 200 | - | kΩ |
| G _m | Maximum critical crystal transconductance | Startup | - | - | 700 | μΑ /V |
| t _{SU(HSE)} | Startup time | V_{DD} is stabilized | - | 2 | - | ms |

Table 39. HSE oscillator characteristics⁽¹⁾

1. Guaranteed by design.

2. Guaranteed by characterization results. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 22*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



Figure 22. HSE oscillator circuit diagram



To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

| Symbol | Parameter | Conditions | Monitored frequency band | Max vs. f _{OSC} /f _{CPU} 8 MHz/32 MHz | Unit | | |
|-----------------------------|------------|--|-----------------------------|---|-----------------|----|------|
| | | <u>)</u> / 2.6.)/ | 0.1 to 30 MHz | -10 | | | |
| S _{EMI} Peak level | Dook lovel | $V_{DD} = 3.6 \text{ v},$ $T_{\Delta} = 25 \text{ °C},$ | 30 to 130 MHz | 5 | dBµV | | |
| | Peak level | LQFP48 package | LQFP48 package | LQFP48 package | 130 MHz to 1GHz | -5 | dBµV |
| | | conforming to IEC61967-2 | EMI Level | 1.5 | - | | |

Table 49. EMI characteristics

6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts \times (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

| Symbol | Ratings | Conditions | Class | Maximum value ⁽¹⁾ | Unit |
|-----------------------|---|--|-------|---------------------------------|------|
| V _{ESD(HBM)} | Electrostatic discharge voltage (human body model) | $T_A = +25 \text{ °C},$ conforming to ANSI/JEDEC JS-001 | 2 | 2000 | V |
| V _{ESD(CDM)} | Electrostatic discharge voltage (charge device model) | $T_A = +25 \text{ °C},$ conforming to ANSI/ESD STM5.3.1. | C4 | 500 | v |

 Table 50. ESD absolute maximum ratings

1. Guaranteed by characterization results.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin



| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit | |
|----------------------------------|----------------------------------|--|---|--------------------|---|----------------------------|--|
| ↓ (3) | Calibration time | f _{ADC} = 16 MHz | 5.2 | | μs | | |
| ^L CAL ⁽¹⁾ | | | | 83 | | 1/f _{ADC} | |
| WLATENCY | | ADC clock = HSI16 | 1.5 ADC cycles + 2 f _{PCLK} cycles | - | 1.5 ADC cycles + 3 f _{PCLK} cycles | - | |
| | ADC_DR register write latency | ADC clock = PCLK/2 | - | 4.5 | - | f _{PCLK} cycle | |
| | | ADC clock = PCLK/4 | - | 8.5 | - | f _{PCLK} cycle | |
| | | f _{ADC} = f _{PCLK} /2 = 16 MHz 0.266 | | | | μs | |
| | | $f_{ADC} = f_{PCLK}/2$ | 8.5 | | | 1/f _{PCLK} | |
| t _{latr} (3) | Trigger conversion latency | $f_{ADC} = f_{PCLK}/4 = 8 \text{ MHz}$ | | μs | | | |
| | | $f_{ADC} = f_{PCLK}/4$ | 16.5 | | | 1/f _{PCLK} | |
| | | f _{ADC} = f _{HSI16} = 16 MHz | 0.252 | - | 0.260 | μs | |
| Jitter _{ADC} | ADC jitter on trigger conversion | f _{ADC} = f _{HSI16} | - | 1 | - | 1/f _{HSI16} | |
| + (3) | Sompling time | f _{ADC} = 16 MHz | 0.093 | - 10.03 | | μs | |
| t _S ''' | | | 1.5 | - | 239.5 | 1/f _{ADC} | |
| t _{STAB} ⁽³⁾ | Power-up time | | 0 | 0 | 1 | μs | |
| | Total conversion time | f _{ADC} = 16 MHz | 0.875 | | 10.81 | μs | |
| t _{ConV} ⁽³⁾ | (including sampling time) | | 14 to 173 (t _S fo successive app | r sampl roximat | ampling +12.5 for ximation) | | |

Table 57. ADC characteristics (continued)

1. V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to *Table 58: RAIN max for fADC* = 16 *MHz*.

2. A current consumption proportional to the APB clock frequency has to be added (see *Table 34: Peripheral current consumption in Run or Sleep mode*).

3. Guaranteed by design.

 Standard channels have an extra protection resistance which depends on supply voltage. Refer to Table 58: RAIN max for fADC = 16 MHz.

Equation 1: $R_{AIN} max$ formula

$$R_{AIN} < \frac{r_{S}}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).



7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status *are available at http://www.st.com.* ECOPACK[®] is an ST trademark.

7.1 LQFP48 package information



Figure 34. LQFP48, 7 x 7 mm, 48-pin low-profile quad flat package outline

1. Drawing is not to scale.



LQFP32 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



7.3 UFQFPN32 package information



Figure 40. UFQFPN32, 5 x 5 mm, 32-pin package outline

1. Drawing is not to scale.

Table 72. UFQFPN32, 5 x 5 mm, 32-pin package mechanical data

| Symbol | | millimeters | | inches ⁽¹⁾ | | |
|--------|-------|-------------|-------|-----------------------|--------|--------|
| | Min | Тур | Max | Min | Тур | Max |
| А | 0.500 | 0.550 | 0.600 | 0.0197 | 0.0217 | 0.0236 |
| A1 | 0.000 | 0.020 | 0.050 | 0.0000 | 0.0008 | 0.0020 |
| A3 | - | 0.200 | - | - | 0.0079 | - |
| b | 0.180 | 0.250 | 0.300 | 0.0071 | 0.0098 | 0.0118 |
| D | 4.900 | 5.000 | 5.100 | 0.1929 | 0.1969 | 0.2008 |
| D2 | 3.200 | 3.450 | 3.700 | 0.1260 | 0.1358 | 0.1457 |
| E | 4.900 | 5.000 | 5.100 | 0.1929 | 0.1969 | 0.2008 |
| E2 | 3.200 | 3.450 | 3.700 | 0.1260 | 0.1358 | 0.1457 |
| е | - | 0.500 | - | - | 0.0197 | - |
| L | 0.300 | 0.400 | 0.500 | 0.0118 | 0.0157 | 0.0197 |
| ddd | - | - | 0.080 | - | - | 0.0031 |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Table 74. WLCSP25 - 2.097 x 2.493 mm, 0.400 mm pitch wafer level chip scale mechanical data

| Symbol | | Milimeters | | Inches ⁽¹⁾ | | | |
|--------|--------|------------|-----|-----------------------|-----|-----|--|
| | Min | Тур | Мах | Min | Тур | Мах | |
| aaa | 0.1000 | - | - | 0.0039 | - | - | |
| bbb | 0.1000 | - | - | 0.0039 | - | - | |
| CCC | 0.1000 | - | - | 0.0039 | - | - | |
| ddd | 0.0500 | - | - | 0.0020 | - | - | |
| eee | 0.0500 | - | - | 0.0020 | - | - | |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

2. Back side coating.

3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.





Table 75. WLCSP25 recommended PCB design rules

| Dimension | Recommended values |
|----------------|---|
| Pitch | 0.4 mm |
| Dpad | 260 μm max. (circular) 220 μm recommended |
| Dsm | 300 μm min. (for 260 μm diameter pad) |
| PCB pad design | Non-solder mask defined via underbump allowed |



7.6 TSSOP20 package information





1. Drawing is not to scale.

| Table 76. TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch, |
|---|
| package mechanical data |

| Symbol | | millimeters | | | inches ⁽¹⁾ | |
|--------|-------|-------------|-------|--------|-----------------------|--------|
| Symbol | Min. | Тур. | Max. | Min. | Тур. | Max. |
| A | - | - | 1.200 | - | - | 0.0472 |
| A1 | 0.050 | - | 0.150 | 0.0020 | - | 0.0059 |
| A2 | 0.800 | 1.000 | 1.050 | 0.0315 | 0.0394 | 0.0413 |
| b | 0.190 | - | 0.300 | 0.0075 | - | 0.0118 |
| С | 0.090 | - | 0.200 | 0.0035 | - | 0.0079 |
| D | 6.400 | 6.500 | 6.600 | 0.2520 | 0.2559 | 0.2598 |
| E | 6.200 | 6.400 | 6.600 | 0.2441 | 0.2520 | 0.2598 |
| E1 | 4.300 | 4.400 | 4.500 | 0.1693 | 0.1732 | 0.1772 |
| е | - | 0.650 | - | - | 0.0256 | - |
| L | 0.450 | 0.600 | 0.750 | 0.0177 | 0.0236 | 0.0295 |
| L1 | - | 1.000 | - | - | 0.0394 | - |



TSSOP20 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



9 Revision history

| Date | Revision | Changes |
|-------------|----------|---|
| 18-Sep-2015 | 1 | Initial release. |
| | | Datasheet status changed to production data.Updated power consumption in run mode on cover page. Updated <i>Table 5: Functionalities depending on the working mode</i> |
| | | (from Run/active down to standby). |
| | | <i>Table 15: Pin definitions.</i> |
| | | Updated power dissipation (P _D) in <i>Table 20: General operating conditions</i> . |
| | | Updated current consumption with all peripherals enabled in <i>Table 34: Peripheral current consumption in Run or Sleep mode</i> and <i>Table 35: Peripheral current consumption in Stop and Standby mode</i> . Modified t _{WSTOP} for f _{HCLK} =65 MHz in <i>Table 36: Low-power mode wakeup timings</i> . |
| 22-Oct-2015 | 2 | Updated Table 24: Current consumption in Run mode, code with data processing running from Flash memory, Table 25: Current consumption in Run mode vs code type, code with data processing running from Flash memory, Figure 15: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE = 16 MHz, 1WS and Figure 16: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS. |
| | | Updated Table 26: Current consumption in Run mode, code with data processing running from RAM and Table 27: Current consumption in Run mode vs code type, code with data processing running from RAM, Table 28: Current consumption in Sleep mode. |
| | | Updated Table 29: Current consumption in Low-power run mode and Figure 17: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Low- power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS. Updated Table 30: Current consumption in Low-power Sleep mode. |
| | | Updated Table 31: Typical and maximum current consumptions in Stop mode, Table 32: Typical and maximum current consumptions in Standby mode, Figure 18: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 19: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks off. |
| | | Updated Table 48: EMS characteristics and Table 49: EMI characteristics. |

Table 79. Document revision history

